

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	310	(252/587).CCLS.	USPAT
2	BRS	L2	13117	microprocessor and infrared	USPAT
3	BRS	L3	206	microprocessor and ((infrared or IR) with shield\$4)	USPAT
4	BRS	L4	10	microprocessor and ((infrared or IR) adj shield\$4)	USPAT
5	BRS	L5	7	CPU and ((infrared or IR) adj shield\$4)	USPAT
6	IS&R	L6	618	(257/777).CCLS.	USPAT
7	BRS	L7	3	6 and (smart adj card)	USPAT
8	BRS	L8	700	infrared and (smart adj card)	USPAT
9	BRS	L9	0	(block adj infrared) same (smart adj card)	USPAT
10	BRS	L10	0	(infrared adj shield\$4) same (smart adj card)	USPAT
11	BRS	L11	0	(IR adj shield\$4) same (smart adj card)	USPAT
12	BRS	L12	0	(IR with shield\$4) same (smart adj card)	USPAT
13	BRS	L13	0	(infrared with shield\$4) same (smart adj card)	USPAT
14	BRS	L14	2	(infrared with shield\$4) same CPU	USPAT
15	BRS	L15	0	(infrared with shield\$4) same (plastic adj card)	USPAT

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	274	(257/679).CCLS.	USPAT
2	IS&R	L2	1	("5394014").PN.	USPAT
3	IS&R	L3	1	("5804827").PN.	USPAT
4	BRS	L4	5	("3971939"   "4313127"   "4519707"   "5122669"   "5581085").PN.	USPAT
5	BRS	L5	2965	radiation adj shield	USPAT
6	BRS	L6	35	5 with silicon	USPAT
7	BRS	L7	1	5 with si	USPAT
8	BRS	L8	1506	shield with silicon	USPAT
9	BRS	L9	35	8 same infrared	USPAT
10	BRS	L10	5	("5166772"   "5317195"   "5557142"   "6086979"   "6261919").PN.	USPAT
11	BRS	L11	2622	shield\$4 with silicon	USPAT
12	BRS	L12	58	11 same infrared	USPAT
13	BRS	L13	4	("5189500"   "5504376"   "5779918"   "6259083").PN.	USPAT
14	BRS	L14	2	5804827.URPN.	USPAT
15	BRS	L15	478	shield\$4 with si	USPAT
16	BRS	L16	4	15 same infrared	USPAT
17	BRS	L17	4487	smart adj card	USPAT
18	BRS	L18	17	17 and (shield\$4 same infrared)	USPAT
19	IS&R	L19	618	(257/777).CCLS.	USPAT
20	BRS	L20	51	19 and infrared	USPAT
21	BRS	L21	1	20 and shield\$4	USPAT
22	BRS	L22	3	15 same IR	USPAT

\* NOTICES \*

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1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. \*\*\*\* shows the word which can not be translated.
3. In the drawings, any words are not translated.

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CLAIMS

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[Claim(s)]

[Claim 1] The semiconductor device characterized by having the protective coat which consists of a semiconductor chip equipped with the integrated circuit, and a binder which was formed on this and contained the particle, distributing irregularity with a level difference [ by the aforementioned particle ] of 2 micrometers or more, and forming it in the aforementioned protective coat front face.

[Claim 2] The semiconductor device with which perpendicular projected area of the aforementioned protective coat thick direction of the aforementioned particle to the area of the aforementioned protective coat is characterized by being less than 60% in a semiconductor device according to claim 1.

[Claim 3] It is the semiconductor device which the aforementioned particle consists of a ceramic in a semiconductor device according to claim 1 or 2, and is characterized by the mean particle diameter being 2 micrometers or more.

[Claim 4] It is the semiconductor device characterized by the aforementioned ceramic consisting of a silica, an alumina, a mica, titanium oxide, a silicon carbide, a titanium carbide, a tungsten carbide, a tantalum carbide, a boron carbide, a silicon nitride, boron nitride, a titanium nitride, or a nitriding tungsten in a semiconductor device according to claim 3.

[Claim 5] It is the semiconductor device characterized by the aforementioned binder consisting of thermosetting resin, an inorganic hardenability material, or an inorganic glass material in a semiconductor device a claim 1 - given in 4 any 1 terms.

[Claim 6] SiO<sub>2</sub> in which the aforementioned inorganic hardenability material is formed of oxidization of polysilazane in a semiconductor device according to claim 5 Semiconductor device characterized by carrying out shell composition.

[Claim 7] The semiconductor device with which it is characterized by the aforementioned thermosetting resin consisting of a fluororesin, a polyphenylene ether, a polyimide, or silicone resin in a semiconductor device according to claim 5.

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[Translation done.]